

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s) : H. S. YANG, et al.

Group Art Unit: 2812

Appln. No. : 10/707,842

Examiner: W. L. Lindsay Jr.

Filed : January 16, 2004

For : METHOD AND APPARATUS TO INCREASE STRAIN EFFECT IN A
TRANSISTOR CHANNEL

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
U.S. Patent and Trademark Office
Customer Service Window, Mail Stop Amendment
Randolph Building
401 Dulany Street
Alexandria, VA 22314
Sir:

In accordance with the duty of disclosure under 37 C.F.R. § 1.56, and supplemental to the Information Disclosure Statement filed on August 30, 2005, applicant respectfully brings the following documents, listed on the attached form PTO-1449, to the attention of the Examiner in charge of the above-identified application.

Further to the U.S. Patent and Trademark Office's decision to waive the requirement under 37 C.F.R. § 1.98 (a)(2)(i), copies of the U.S. patents and U.S. published patent applications are not enclosed herewith. However, if any copies are needed, the Examiner is respectfully requested to contact the undersigned. Copies of non-US patent documents as well as the documents listed in the "Other Documents" section of the attached PTO-1449 are enclosed.

Applicants respectfully request that the Examiner consider the materials cited and indicate such consideration by appropriately initialing the enclosed PTO-1449 Form and including a copy of the initialed form in the next official communication.

Applicants note that this Information Disclosure Statement is being after receipt of a first action on the merits from the U.S. Patent and Trademark Office. Accordingly, please charge the required fee of \$180.00 to **IBM Deposit Account No. 09-0458** (Fishkill).

Should the US Patent & Trademark Office conclude that other fees are required, authorization is hereby given to charge to **IBM Deposit Account No. 09-0458** (Fishkill) any fee necessary to ensure consideration of these materials.

Should there be any questions concerning this application, the Examiner is invited to contact the undersigned at the below listed telephone number.

Respectfully submitted,
H. S. YANG, et al.

A handwritten signature in black ink, appearing to read 'Andrew M. Calderon', written over a horizontal line.

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May 15, 2006
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| FORM PTO-1449 | | U.S. Department of Commerce Patent and Trademark Office | | Atty. Docket No. FIS920030238 | | Application No. 10/707,842 | |
| INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary) | | | | Applicant Haining S. YANG, et al. | | | |
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